AMENDMENTS TO THE CLAIMS

1. **(Previously presented)** A thick film photoresist composition comprising:

(A) a resin component containing (a) from 61 to 90% by weight of a structural unit derived from a cyclic alkyl (meth)acrylate ester, and (b) a structural unit derived from a radical polymerizable compound containing a hydroxyl group;

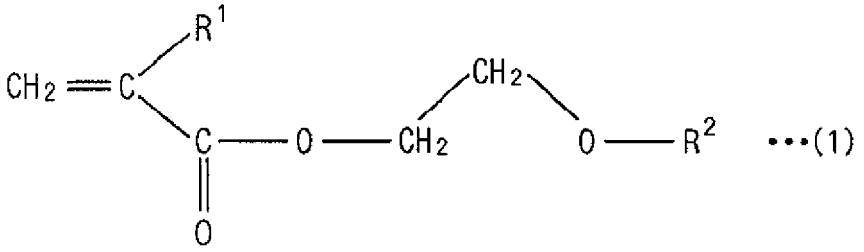
(B) a polymerizable compound containing at least one ethylenic unsaturated double bond;

(C) a photopolymerization initiator; and

(D) an organic solvent.

2. **(Original)** A thick film photoresist composition according to claim 1, wherein said structural unit (b) accounts for at least 1% by weight, but less than 10% by weight, of said component (A).

3. **(Original)** A thick film photoresist composition according to claim 1, wherein said component (A) further comprises (c) a structural unit derived from a radical polymerizable compound represented by a general formula (1) shown below:



(wherein, R^1 represents a hydrogen atom or a methyl group, and R^2 represents a hydrogen atom or an alkyl group of 1 to 4 carbon atoms).

4. **(Previously presented)** A thick film photoresist composition according to claim 1, wherein said component (D) is methyl isobutyl ketone and/or methyl ethyl ketone.

5. **(Currently amended)** A method of forming a resist pattern, comprising forming a resist layer comprising said resist composition on a substrate, exposing the resist layer to ultraviolet light or visible light through a mask with a predetermined pattern, and developing the exposed resist layer using an aqueous alkali solution as the developing solution, wherein said resist pattern is formed using a thick film photoresist composition according to any one of claim 1 through claim 4.

6. **(Previously presented)** A pattern formed using the method according to claim 5.